

**INSULATED GATE BIPOLAR TRANSISTOR WITH
 ULTRAFAST SOFT RECOVERY DIODE**
Features

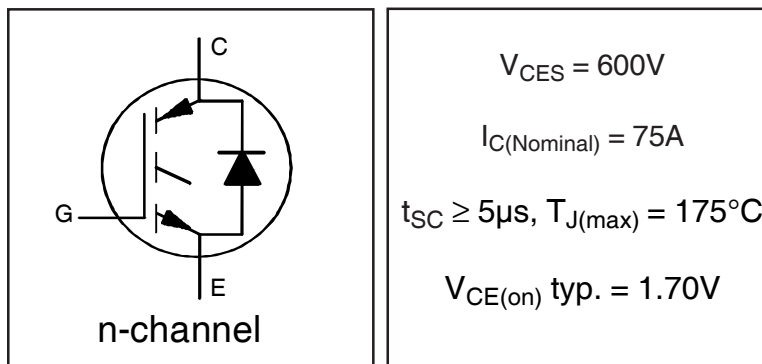
- Low $V_{CE(ON)}$ Trench IGBT Technology
- Low switching losses
- Maximum Junction temperature 175 °C
- 5 μ S short circuit SOA
- Square RBSOA
- 100% of the parts tested for 4X rated current (I_{LM})
- Positive $V_{CE(ON)}$ Temperature Coefficient
- Soft Recovery Co-Pak Diode
- Tight parameter distribution
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Benefits

- High Efficiency in a wide range of applications
- Suitable for a wide range of switching frequencies due to Low $V_{CE(ON)}$ and Low Switching losses
- Rugged transient Performance for increased reliability
- Excellent Current sharing in parallel operation
- Low EMI

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

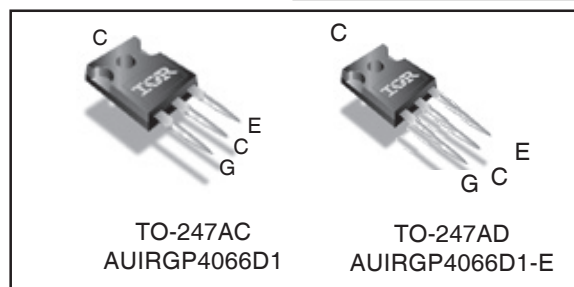


$V_{CES} = 600V$

$I_{C(Nominal)} = 75A$

$t_{SC} \geq 5\mu s, T_{J(max)} = 175^\circ C$

$V_{CE(on)} \text{ typ.} = 1.70V$



G	C	E
Gate	Collector	Emitter

	Parameter	Max.	Units	
V_{CES}	Collector-to-Emitter Voltage	600	V	
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	140	A	
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	90		
$I_{NOMINAL}$	Nominal Current	75		
I_{CM}	Pulse Collector Current $V_{GE} = 15V$	225		
I_{LM}	Clamped Inductive Load Current $V_{GE} = 20V$ ①	300		
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	140		
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	90		
I_{FM}	Diode Maximum Forward Current ②	300		
V_{GE}	Continuous Gate-to-Emitter Voltage	± 20		V
	Transient Gate-to-Emitter Voltage	± 30		
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	454	W	
		227		
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C	
		Soldering Temperature, for 10 sec.		300 (0.063 in. (1.6mm) from case)
	Mounting Torque, 6-32 or M3 Screw	10 lbf-in (1.1 N-m)		

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ④	—	—	0.33	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode) ④	—	—	0.53	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	40	—	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 200μA ④
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.78	—	V/°C	V _{GE} = 0V, I _C = 10mA (25°C-175°C)
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	1.70	2.1	V	I _C = 75A, V _{GE} = 15V, T _J = 25°C ②
		—	2.0	—		I _C = 75A, V _{GE} = 15V, T _J = 150°C②
		—	2.1	—		I _C = 75A, V _{GE} = 15V, T _J = 175°C②
V _{GE(th)}	Gate Threshold Voltage	4.0	—	6.5	V	V _{CE} = V _{GE} , I _C = 2.1mA
ΔV _{GE(th)} /ΔT _J	Threshold Voltage temp. coefficient	—	-21	—	mV/°C	V _{CE} = V _{GE} , I _C = 2.1mA (25°C - 175°C)
g _f	Forward Transconductance	—	50	—	S	V _{CE} = 50V, I _C = 75A, PW = 25μs
I _{CES}	Collector-to-Emitter Leakage Current	—	3.0	200	μA	V _{GE} = 0V, V _{CE} = 600V
		—	10	—	mA	V _{GE} = 0V, V _{CE} = 600V, T _J = 175°C
V _{FM}	Diode Forward Voltage Drop	—	1.60	1.77	V	I _F = 75A
		—	1.54	—		I _F = 75A, T _J = 175°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	150	225	nC	I _C = 75A V _{GE} = 15V V _{CC} = 400V
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	40	60		
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	60	90		
E _{on}	Turn-On Switching Loss	—	4240	5190	μJ	I _C = 75A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 100μH, T _J = 25°C Energy losses include tail & diode reverse recovery
E _{off}	Turn-Off Switching Loss	—	2170	3060		
E _{total}	Total Switching Loss	—	6410	8250		
t _{d(on)}	Turn-On delay time	—	50	70	ns	I _C = 75A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 100μH T _J = 25°C
t _r	Rise time	—	80	100		
t _{d(off)}	Turn-Off delay time	—	200	230		
t _f	Fall time	—	60	80		
E _{on}	Turn-On Switching Loss	—	6210	—	μJ	I _C = 75A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 100μH, T _J = 175°C Energy losses include tail & diode reverse recovery
E _{off}	Turn-Off Switching Loss	—	2815	—		
E _{total}	Total Switching Loss	—	9025	—		
t _{d(on)}	Turn-On delay time	—	45	—	ns	I _C = 75A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 100μH T _J = 175°C
t _r	Rise time	—	70	—		
t _{d(off)}	Turn-Off delay time	—	240	—		
t _f	Fall time	—	80	—		
C _{ies}	Input Capacitance	—	4470	—	pF	V _{GE} = 0V V _{CC} = 30V f = 1.0Mhz
C _{oes}	Output Capacitance	—	350	—		
C _{res}	Reverse Transfer Capacitance	—	140	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T _J = 175°C, I _C = 300A V _{CC} = 480V, V _p ≤ 600V R _G = 10Ω, V _{GE} = +20V to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	V _{CC} = 400V, V _p ≤ 600V R _G = 10Ω, V _{GE} = +15V to 0V
E _{rec}	Reverse Recovery Energy of the Diode	—	680	—	μJ	T _J = 175°C
t _{rr}	Diode Reverse Recovery Time	—	240	—	ns	V _{CC} = 400V, I _F = 75A
I _{rr}	Peak Reverse Recovery Current	—	50	—	A	V _{GE} = 15V, R _G = 10Ω, L = 100μH

Notes:

- ① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 100μH, R_G = 10Ω.
- ② Pulse width limited by max. junction temperature.
- ③ Refer to AN-1086 for guidelines for measuring V_{(BR)CES} safely.
- ④ R_θ is measured at T_J of approximately 90°C.

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		TO-247AC	N/A
		TO-247AD	
ESD	Machine Model	Class M4 (+/-425V) ^{†††} AEC-Q101-002	
	Human Body Model	Class H2 (+/-4000V) ^{†††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/-1125V) ^{†††} AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage

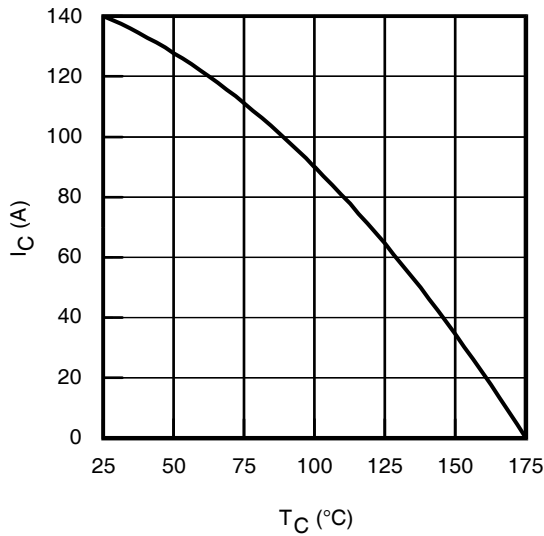


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

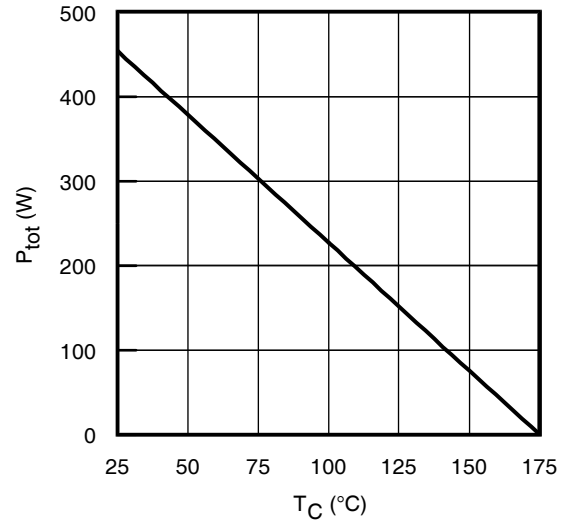


Fig. 2 - Power Dissipation vs. Case Temperature

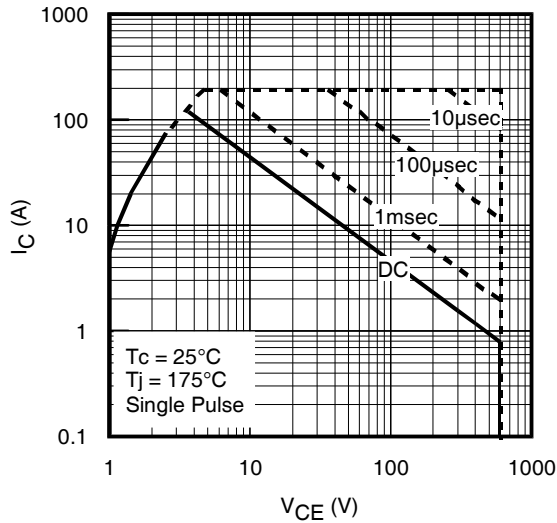


Fig. 3 - Forward SOA
 $T_C = 25^{\circ}C$, $T_J \leq 175^{\circ}C$; $V_{GE} = 15V$

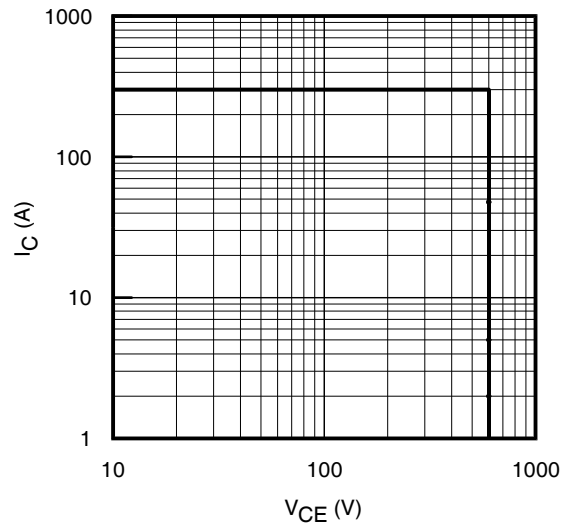


Fig. 4 - Reverse Bias SOA
 $T_J = 175^{\circ}C$; $V_{GE} = 20V$

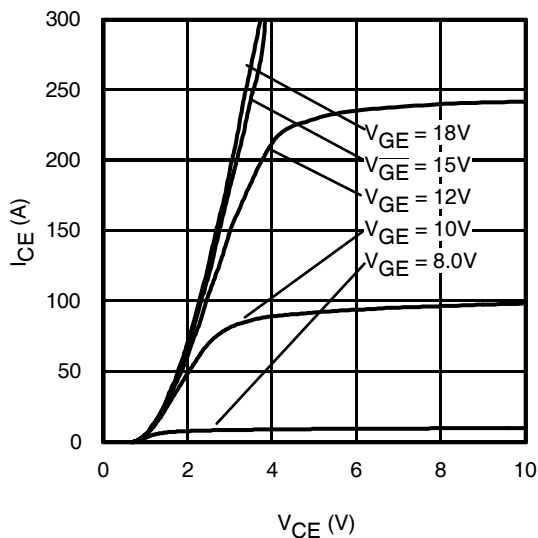


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^{\circ}C$; $t_p \leq 60\mu s$

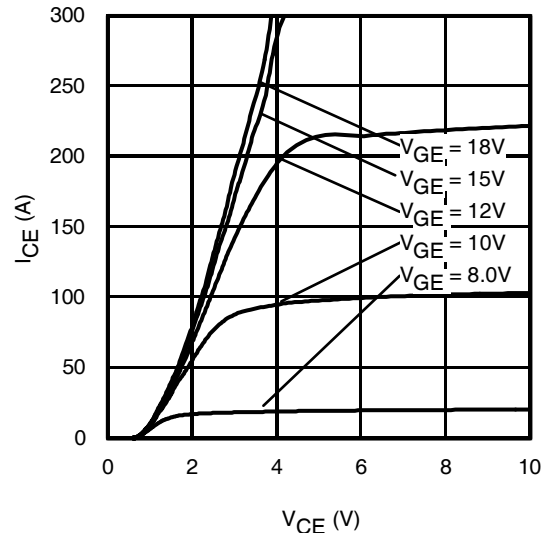


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^{\circ}C$; $t_p \leq 60\mu s$

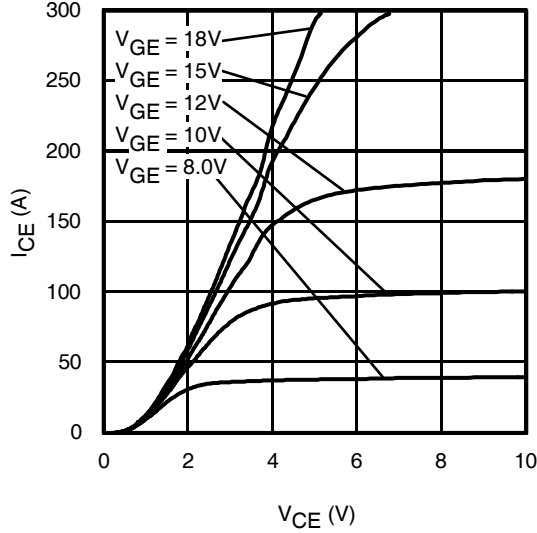


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p \leq 60\mu\text{s}$

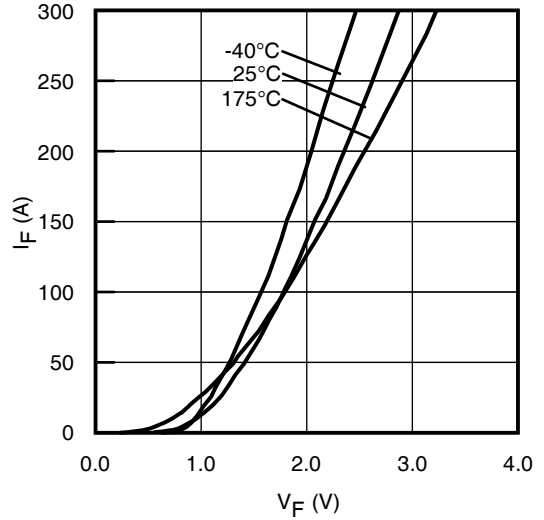


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p \leq 60\mu\text{s}$

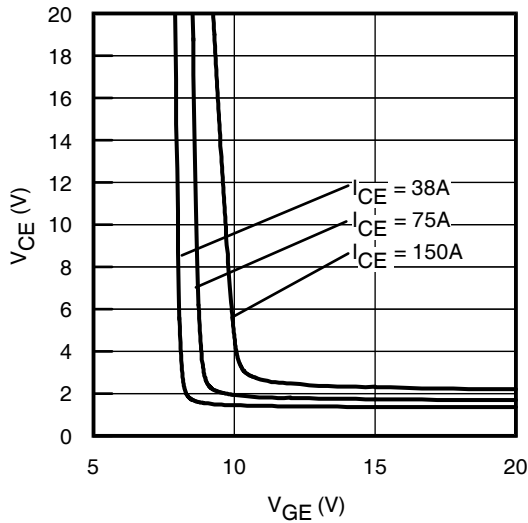


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

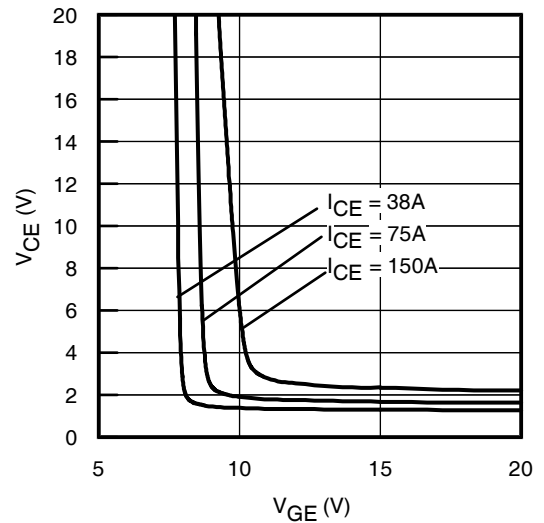


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

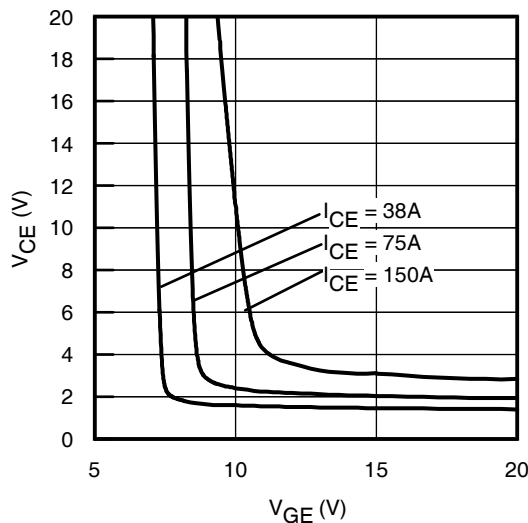


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

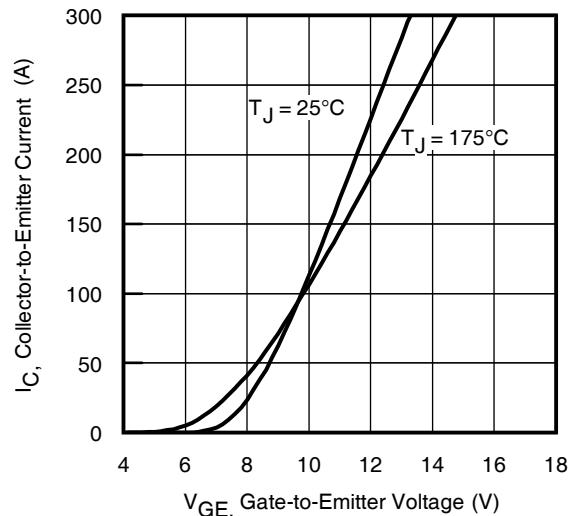


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p \leq 60\mu\text{s}$

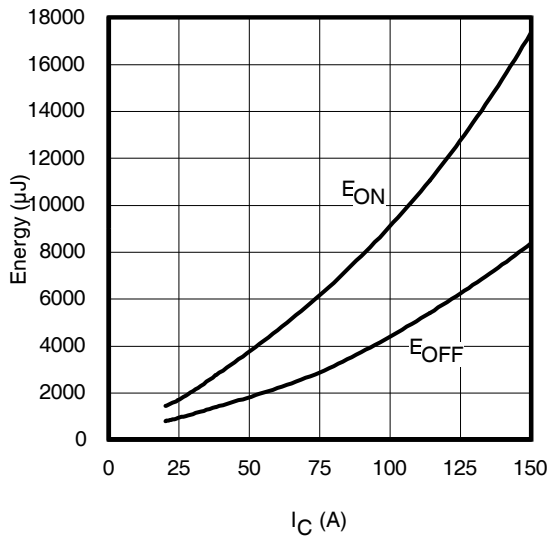


Fig. 13 - Typ. Energy Loss vs. I_C

$T_J = 175^\circ\text{C}$; $L = 100\mu\text{H}$; $V_{CE} = 400\text{V}$, $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

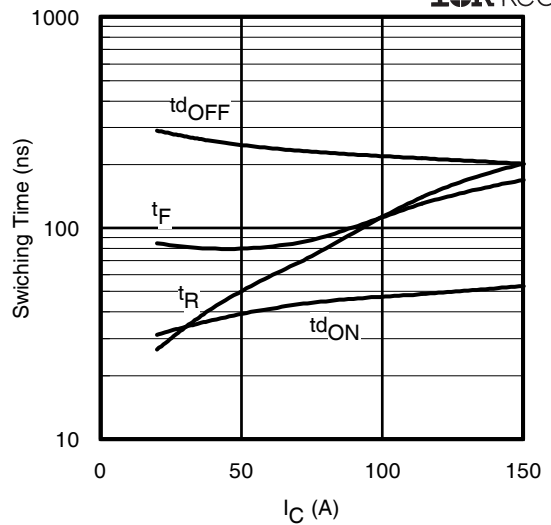


Fig. 14 - Typ. Switching Time vs. I_C

$T_J = 175^\circ\text{C}$; $L = 100\mu\text{H}$; $V_{CE} = 400\text{V}$, $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

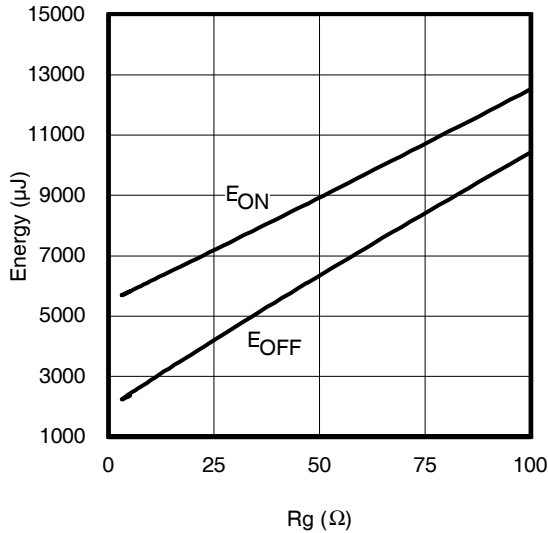


Fig. 15 - Typ. Energy Loss vs. R_G

$T_J = 175^\circ\text{C}$; $L = 100\mu\text{H}$; $V_{CE} = 400\text{V}$, $I_{CE} = 75\text{A}$; $V_{GE} = 15\text{V}$

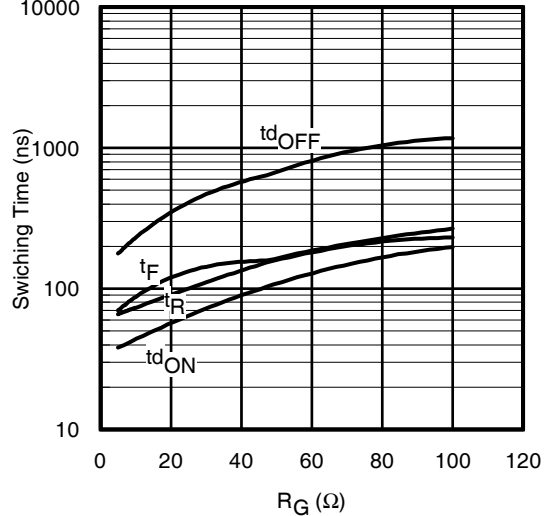


Fig. 16 - Typ. Switching Time vs. R_G

$T_J = 175^\circ\text{C}$; $L = 100\mu\text{H}$; $V_{CE} = 400\text{V}$, $I_{CE} = 75\text{A}$; $V_{GE} = 15\text{V}$

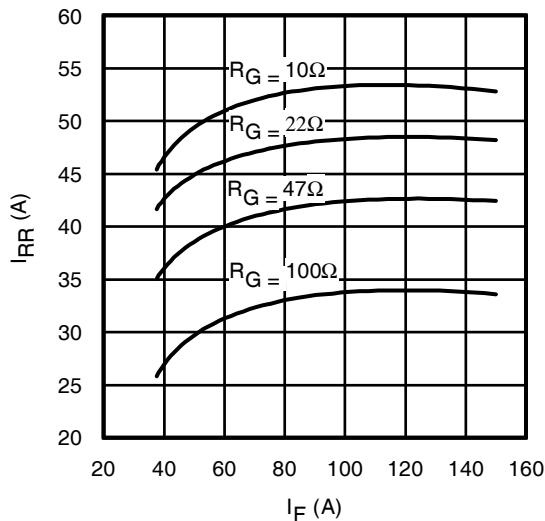


Fig. 17 - Typ. Diode I_{RR} vs. I_F

$T_J = 175^\circ\text{C}$

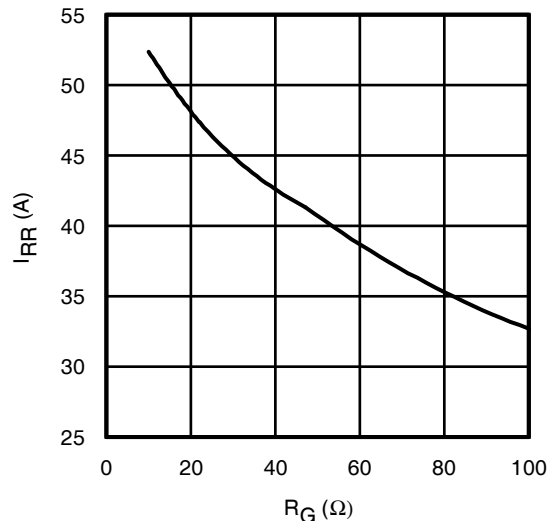


Fig. 18 - Typ. Diode I_{RR} vs. R_G

$T_J = 175^\circ\text{C}$

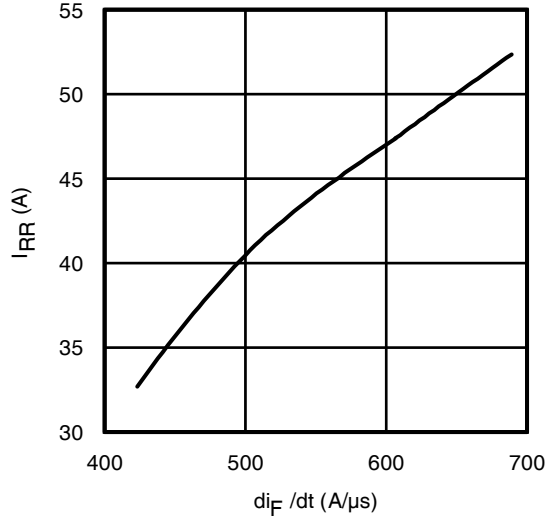


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $I_F = 75A$; $T_J = 175^\circ C$

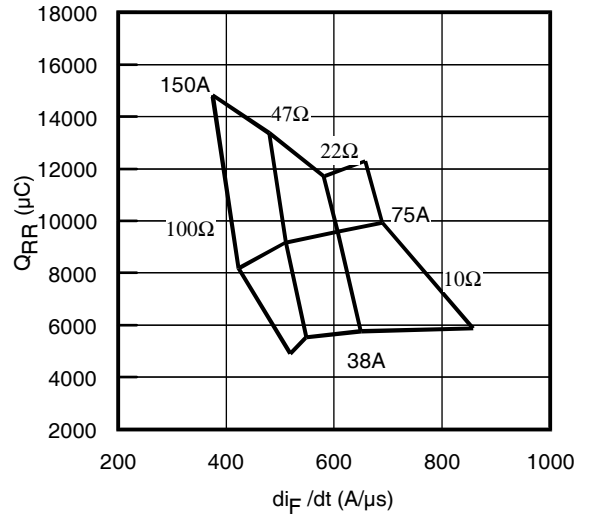


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

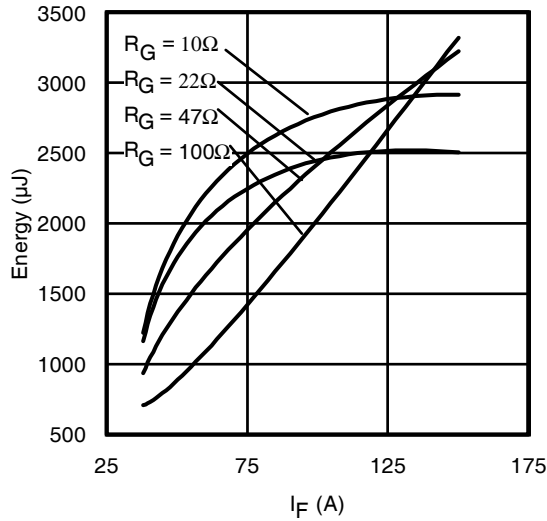


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

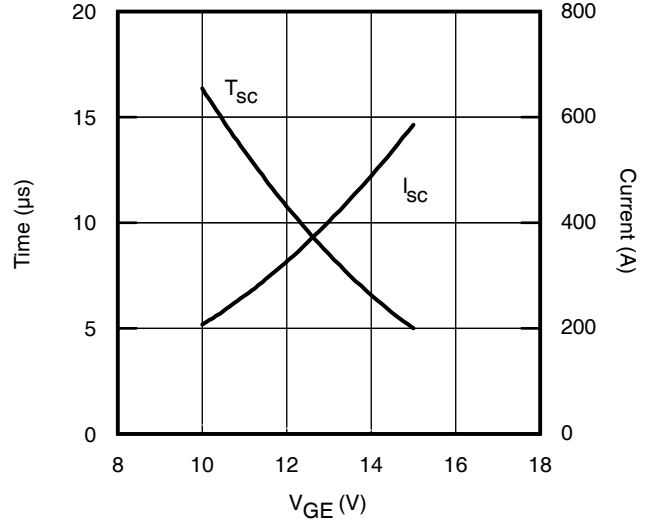


Fig. 22 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$; $T_C = 25^\circ C$

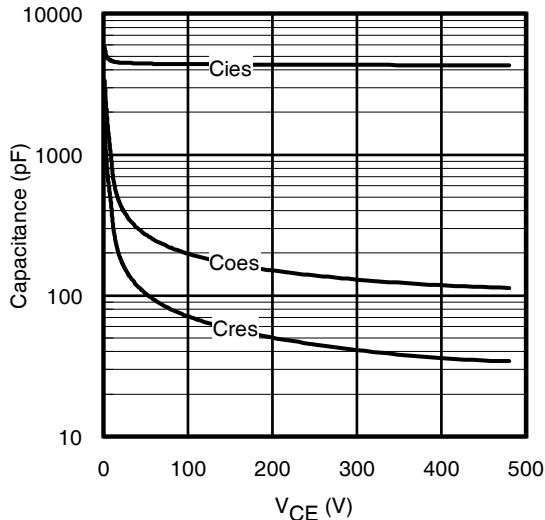


Fig. 23 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

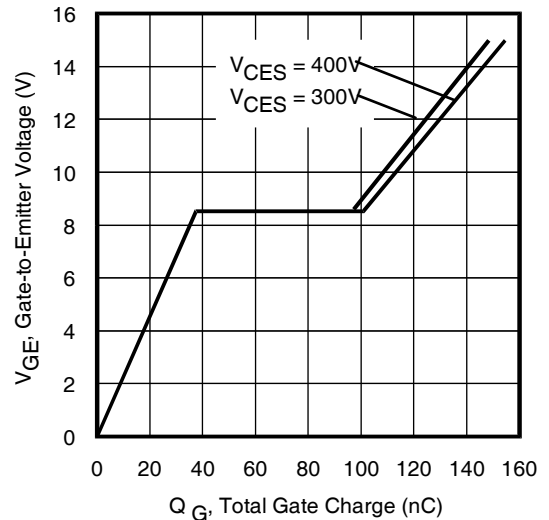


Fig. 24 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 75A$; $L = 485\mu H$

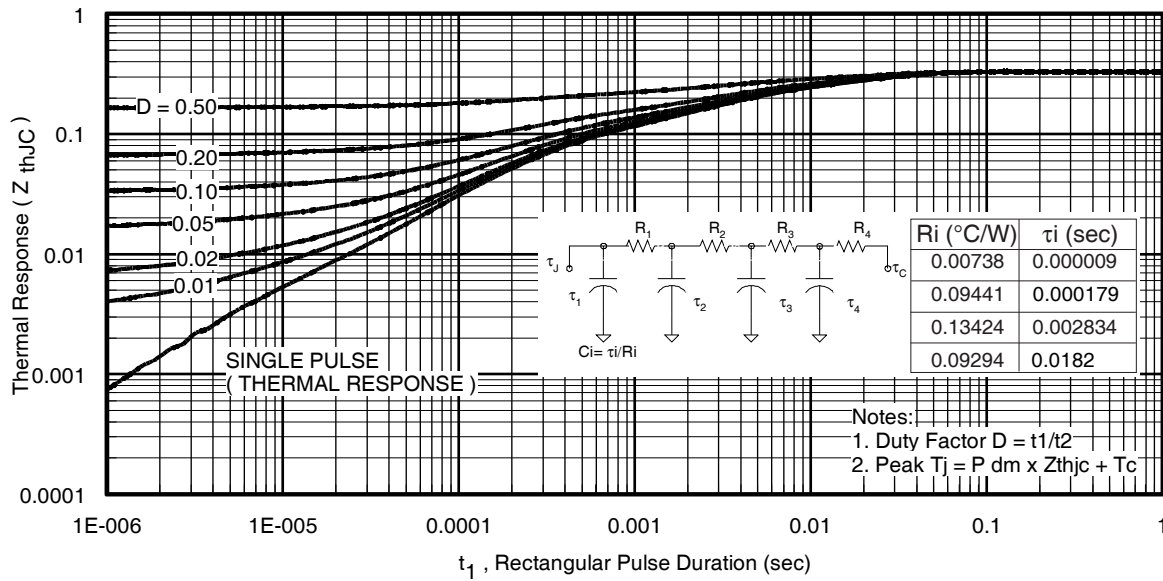


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

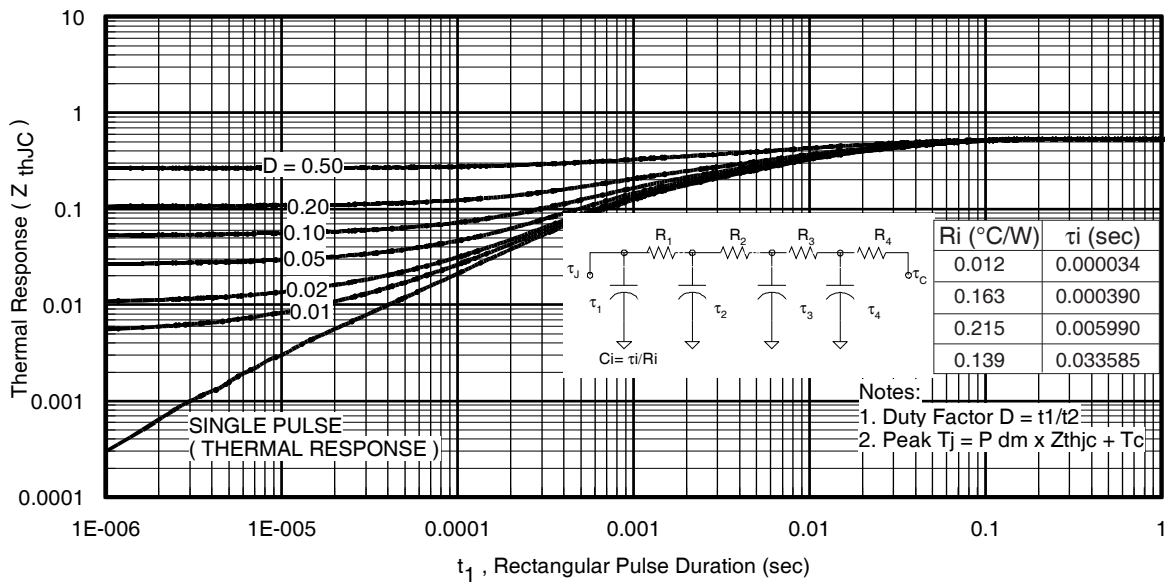


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

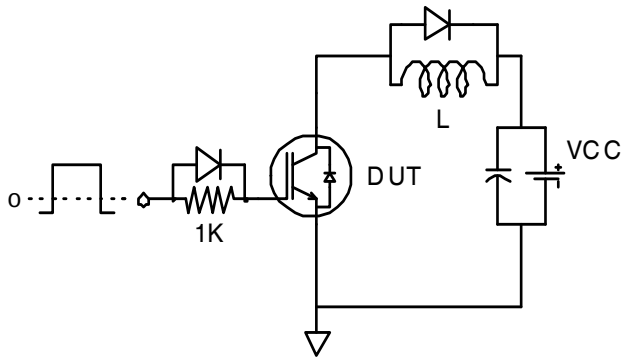


Fig.C.T.1 - Gate Charge Circuit (turn-off)

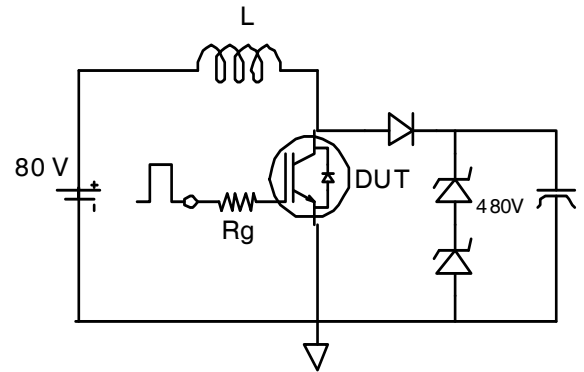


Fig.C.T.2 - RBSOA Circuit

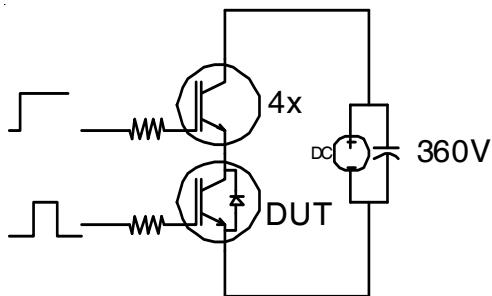


Fig.C.T.3 - S.C. SOA Circuit

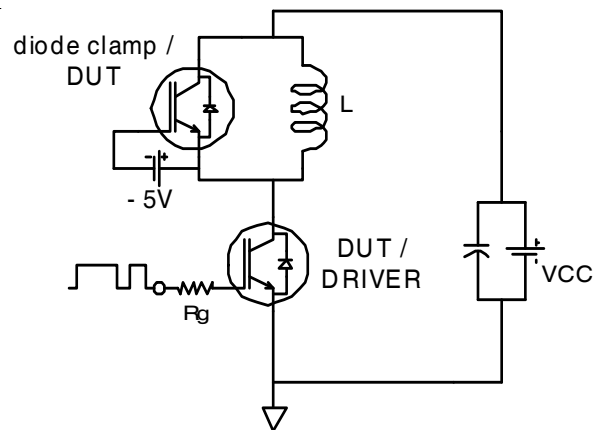


Fig.C.T.4 - Switching Loss Circuit

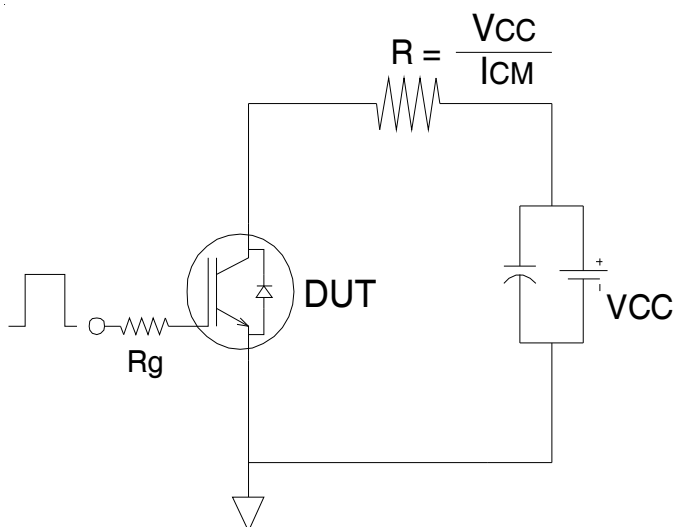


Fig.C.T.5 - Resistive Load Circuit

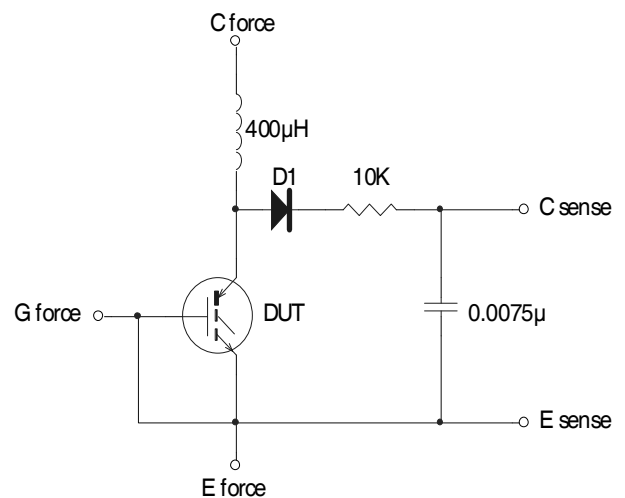


Fig.C.T.6 - BVCES Filter Circuit

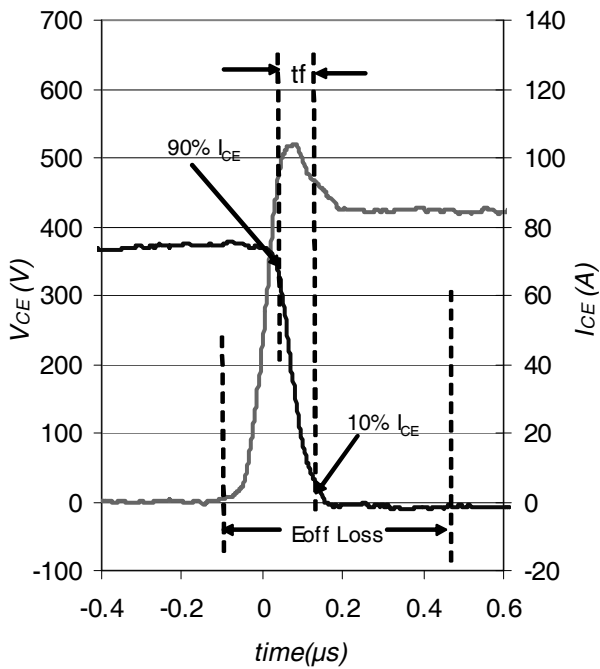


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

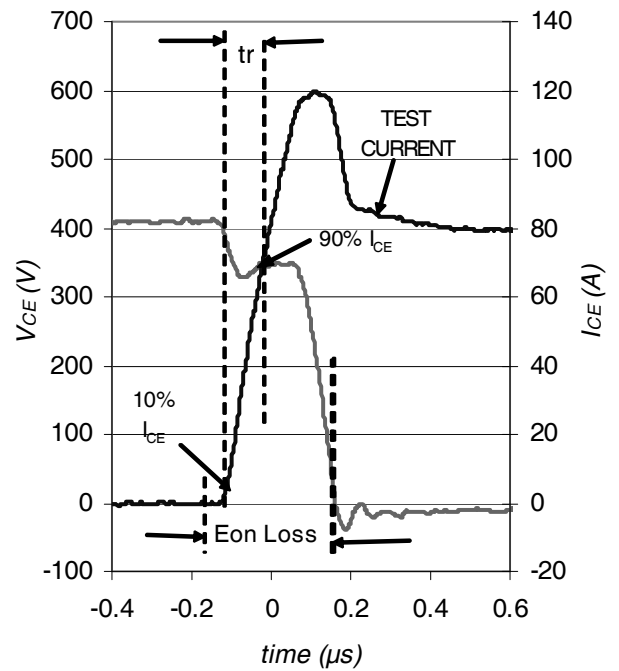


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

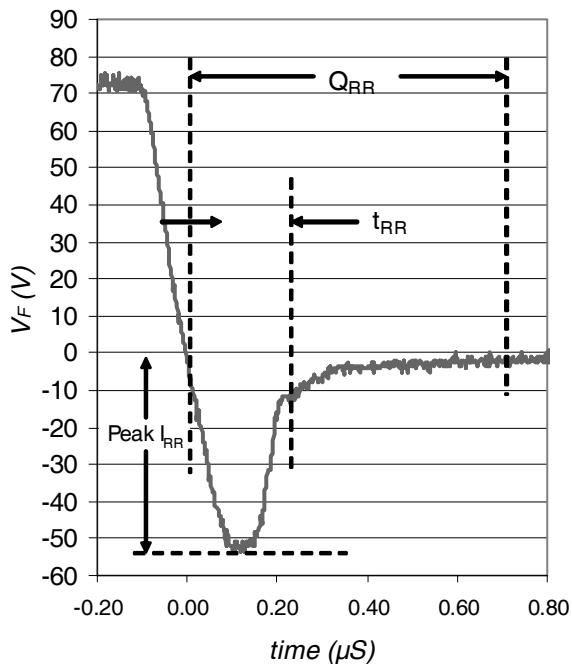


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

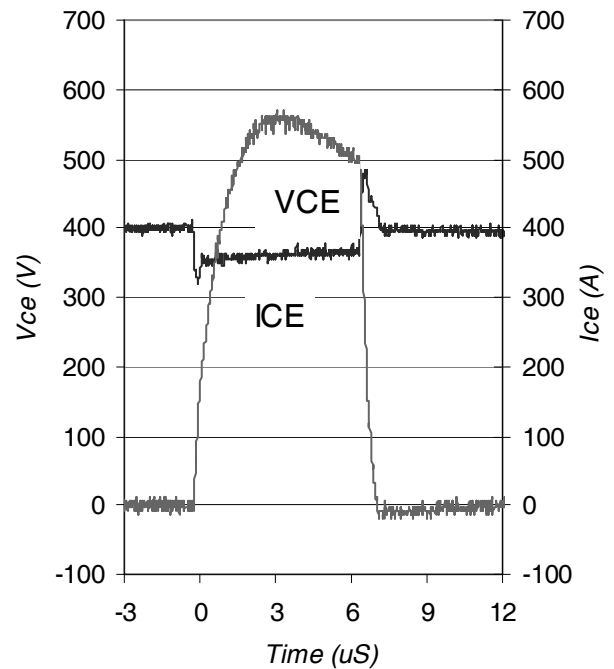
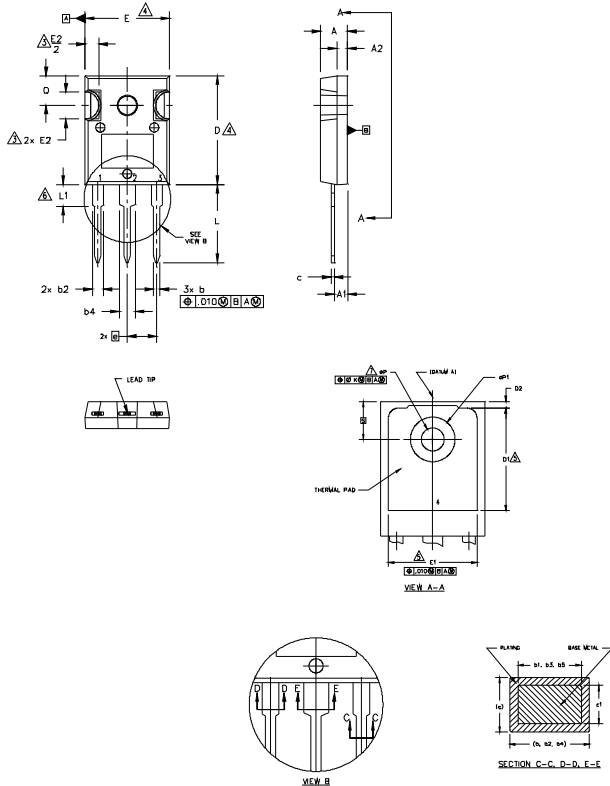


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

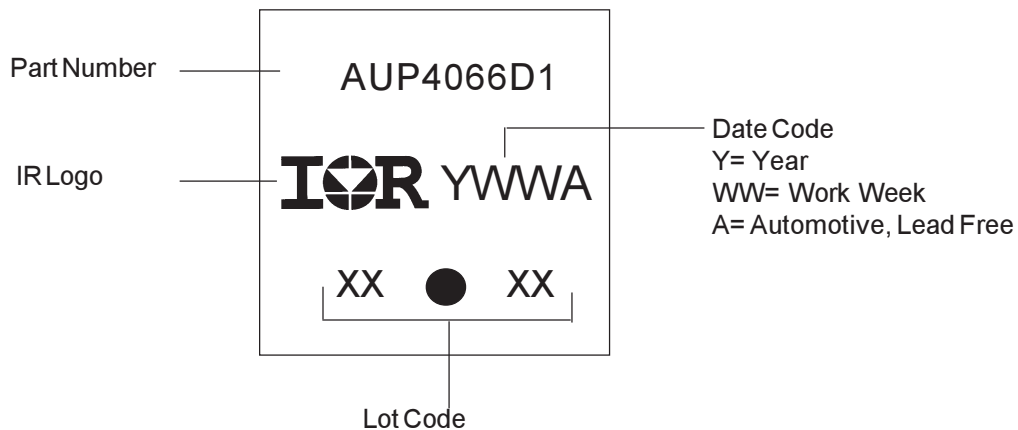
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

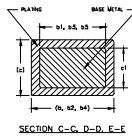
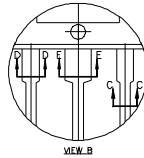
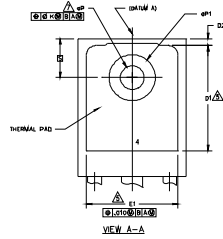
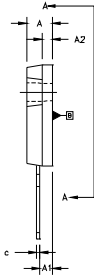
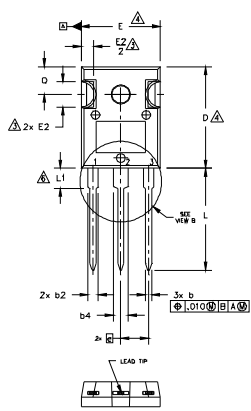


TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN LT.
7. ϕP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES	
	INCHES		MILLIMETERS			
	MIN.	MAX.	MIN.	MAX.		
A	.183	.209	4.65	5.31		
A1	.087	.102	2.21	2.59		
A2	.059	.098	1.50	2.49		
b	.039	.055	0.99	1.40		
b1	.039	.053	0.99	1.35		
b2	.065	.094	1.65	2.39		
b3	.065	.092	1.65	2.34		
b4	.102	.135	2.59	3.43		
b5	.102	.133	2.59	3.38		
c	.015	.035	0.38	0.89		
c1	.015	.033	0.38	0.84		
D	.776	.815	19.71	20.70		4
D1	.515	-	13.08	-		5
D2	.020	.053	0.51	1.35		4
E	.602	.625	15.29	15.87		
E1	.530	-	13.46	-		
E2	.178	.216	4.52	5.49		
e	.215 BSC		5.46 BSC			
ϕk	.010		0.25			
L	.780	.827	19.57	21.00		
L1	.145	.169	3.71	4.29		
ϕP	.140	.144	3.56	3.66		
$\phi P1$	-	.291	-	7.39		
O	.209	.224	5.31	5.69		
S	.217 BSC		5.51 BSC			

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

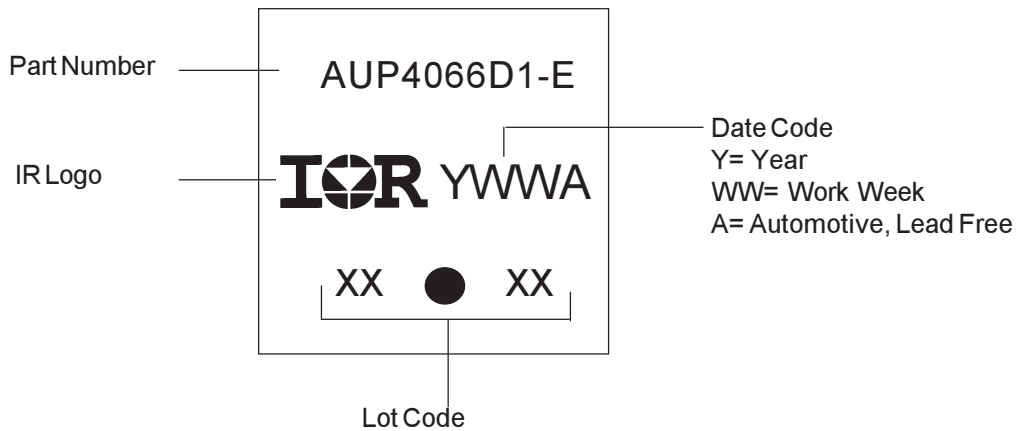
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AD Part Marking Information



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRGP4066D1	TO-247AC	Tube	25	AUIRGP4066D1
AUIRGP4066D1-E	TO-247AD	Tube	25	AUIRGP4066D1-E

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